

KSC1845PBU Datasheet



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DiGi Electronics Part Number KSC1845PBU-DG

Manufacturer onsemi

Manufacturer Product Number KSC1845PBU

Description TRANS NPN 120V 0.05A TO92-3

Detailed Description Bipolar (BJT) Transistor NPN 120 V 50 mA 110MHz 5

00 mW Through Hole TO-92-3



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
KSC1845PBU	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	50 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, Ic:
120 V	300mV @ 1mA, 10mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
50nA (ICBO)	200 @ 1mA, 6V
Power - Max:	Frequency - Transition:
500 mW	110MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 (TO-226AA)	TO-92-3
Base Product Number:	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FAR99	8541 21 0075

NPN Epitaxial Silicon Transistor

KSC1845

Features

- Audio Frequency Low-Noise Amplifier
- Complement to KSA992
- This is a Pb-Free Device

MAXIMUM RATINGS (Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	120	V
V _{CEO}	Collector-Emitter Voltage	120	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	50	mA
Ι _Β	Base Current	10	mA
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

(Values are at T_A = 25°C unless otherwise noted.) (Note 1)

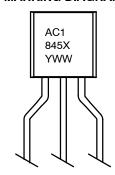
Symbol	Parameter	Value	Unit
P_{D}	Power Dissipation	500	mW
	Derate Above 25°C	4	mW/°C
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	250	°C/W

^{1.} PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.



TO-92 3 4.83x4.76 LEADFORMED CASE 135AR

MARKING DIAGRAM



A = Assembly Code C1845 = Device Code X = F

YWW = Date Code

ORDERING INFORMATION

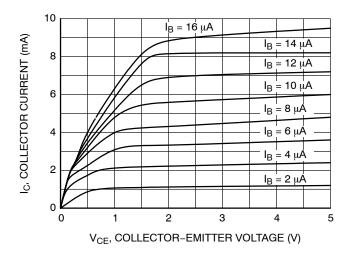
Device	Package	Shipping
KSC1845FTA	TO-92 3 LF (Pb-Free)	2000 / Fan-Fold

ELECTRICAL CHARACTERISTICS (Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_A = 0$	120	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 1 mA, I _B = 0	120	-	-	V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	5	-	-	V
I _{CBO}	Collector Cut-Off Current	V _{CB} = 120 V, I _E = 0	-	-	50	nA
I _{EBO}	Emitter Cut-Off Current	$V_{EB} = 5 \text{ V}, I_{C} = 0$	-	-	50	nA
h _{FE1}	DC Current Gain	$V_{CE} = 6 \text{ V}, I_{C} = 0.1 \text{ mA}$	150	580	-	
h _{FE2}		V _{CE} = 6 V, I _C = 1 mA	300	450	600	
V _{BE} (on)	Base-Emitter On Voltage	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA}$	0.55	0.59	0.65	V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1 mA	-	0.07	0.30	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA}$	50	100	-	MHz
C _{ob}	Output Capacitance	V _{CB} = 30 V, I _E = 0, f = 1 MHz	-	1.6	2.5	pF
NF	Noise Figure	$V_{CE} = -5 \text{ V, } I_{C} = -1.0 \text{ mA,}$ $R_{S} = 100 \text{ k}\Omega, f = 1 \text{ kHz}$	_	7		dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

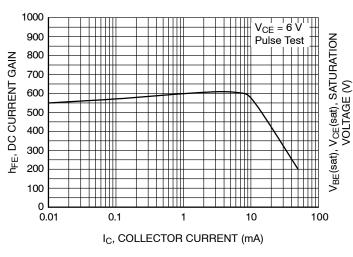
TYPICAL PERFORMANCE CHARACTERISTICS



1.0 $I_B = 1.4 \mu A$ $I_{B}^{\prime} = 1.2 \, \mu A$ IC, COLLECTOR CURRENT (mA) $I_B = 1.0 \mu A$ 8.0 $I_B = 0.8 \mu A$ 0.6 $I_B = 0.6 \, \mu A$ $I_B = 0.4 \mu A$ 0.4 I_B = 0.2 μA 0.2 0 0 20 40 60 80 100 V_{CE}, COLLECTOR-EMITTER VOLTAGE (V)

Figure 1. Static Characteristic

Figure 2. Static Characteristic



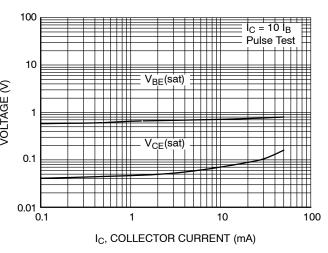
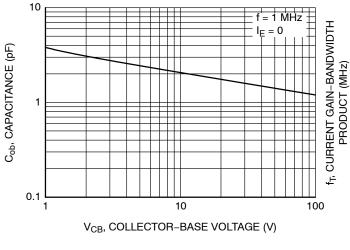


Figure 3. DC Current Gain

Figure 4. Base–Emitter Saturation Voltage and Collector–Emitter Saturation Voltage



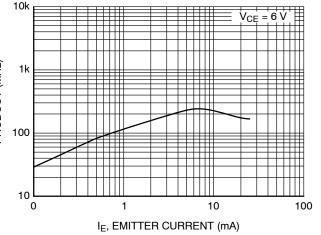
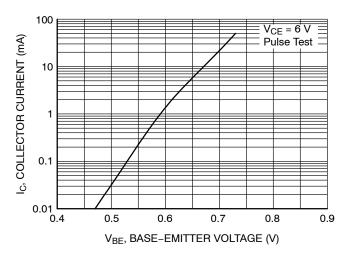


Figure 5. Collector Output Capacitance

Figure 6. Current Gain Bandwidth Product

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)



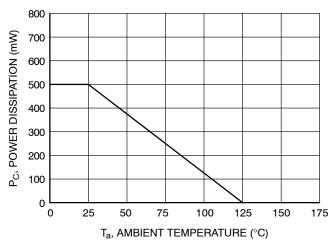


Figure 7. Collector Current vs. Base-Emitter Voltage

Figure 8. Power Derating



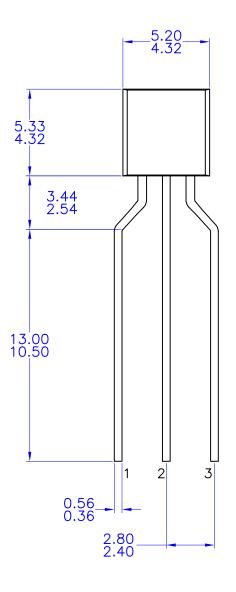
MECHANICAL CASE OUTLINE

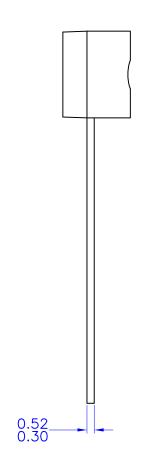
PACKAGE DIMENSIONS

TO-92 3 4.83x4.76 LEADFORMED

CASE 135AR ISSUE O

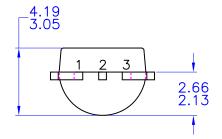
DATE 30 SEP 2016





NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994



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